

AMENDMENTS TO THE CLAIMS

Please amend Claim 1 as indicated below.

1. (Currently Amended) A process of growing a silicon dioxide thin film on a part in a chamber by a sequential chemical vapor deposition process, which comprises a plurality of deposition cycles, each of the cycles comprising in order:

removing gases from the chamber;

exposing the part to a first reactant by introducing a first reactant comprising a gaseous silicon compound that does not contain oxygen into the chamber, wherein the first reactant adsorbs on the part, and wherein the first reactant includes the silicon of the thin film to be formed;

removing gases from the chamber;

exposing the part, coated with the first reactant to atomic hydrogen, wherein the atomic hydrogen reduces the first reactant on the part to silicon;

removing gases from the chamber; and

exposing the part coated with silicon to oxygen, wherein the oxygen converts the silicon on the part to silicon dioxide.

2. (Original) The process of Claim 1, wherein the part is maintained at temperatures of less than 300°C in the chamber.

3. (Original) The process of Claim 1, wherein the first reactant includes a halogen atom.

4. (Original) The process of Claim 3, wherein the first reactant is dichlorosilane.

5. (Original) The process of Claim 1, wherein the first reactant is selected from the group consisting of silane and tetramethylsilane.

6. (Original) The process of Claim 1, wherein the atomic hydrogen is generated in a radical generator in communication with the chamber.

7. (Original) The process of Claim 1, wherein the atomic hydrogen is generated by surrounding the chamber with an RF excitation coil.

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8. (Previously Presented) A process of growing silicon dioxide thin film on a part in a chamber by a sequential chemical vapor deposition process comprising a plurality of deposition cycles, wherein each cycle comprises:

removing gases from the chamber;

introducing a first reactant of gaseous silicon precursor containing oxygen into the chamber to expose the part to the first reactant, wherein the first reactant comprises silicon and oxygen, and wherein the first reactant adsorbs on the part;

removing gases from the chamber;

exposing the part coated with the first reactant to atomic oxygen, wherein the atomic oxygen converts the first reactant on the part to silicon dioxide; and

removing gases from the chamber.

9. (Original) The process of Claim 8, wherein the first reactant is tetraethoxysilane.

10. (Previously Presented) The process of Claim 8, wherein the atomic oxygen is generated in a radical generator in communication with the chamber.

11. (Original) The process of Claim 8, wherein the atomic oxygen is generated by surrounding the chamber with an RF excitation coil.